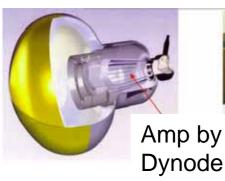
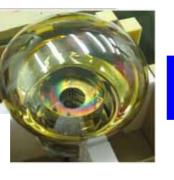
Large Aperture HPD R&D status and future for HK

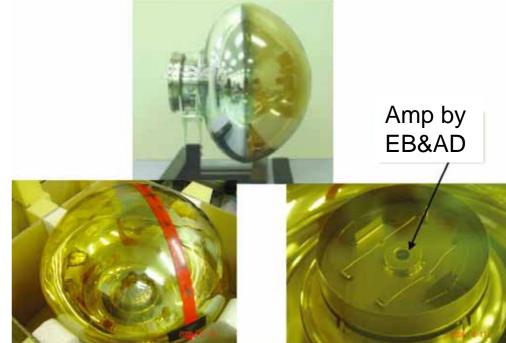
M. Tanaka¹, Y. Kawai³, T. Abe², H. Aihara², H. Kyushima³, M. Suyama³, M. Shiozawa⁴

High Energy Accelerator Research Organization University of Tokyo Hamamatsu Photonics K.K. Institute for Cosmic Ray Research

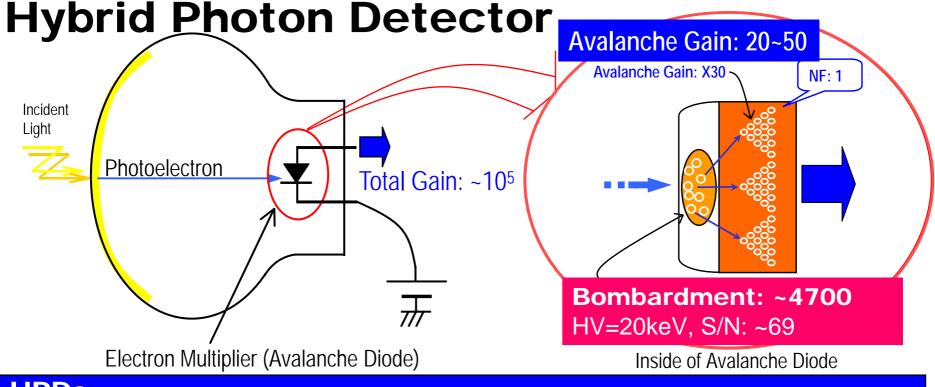




20inch PMT



13inch HPD



HPDs

 \checkmark have a simple structure. \rightarrow lower cost than PMT and easy Quality control.

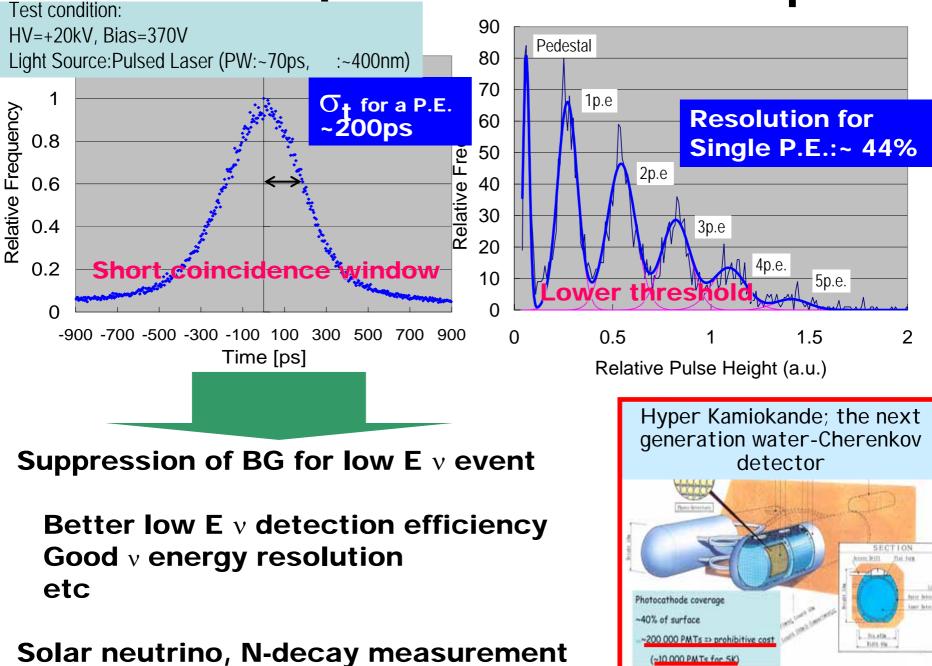
✓ EB takes major role in e-amplification \rightarrow small statistical fluctuation \rightarrow Small Δ path of P.E. \rightarrow Better timing resolution

 \rightarrow Small \triangle gain of P.E. \rightarrow Better S/N

 \checkmark but lower gain \rightarrow a part of readout electronics implementation near HPD

What is Our expected result?

13inch HPD performance and impact



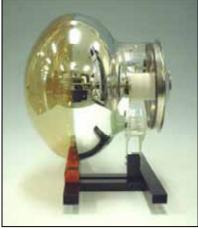
~10 000 PMTs for SK)

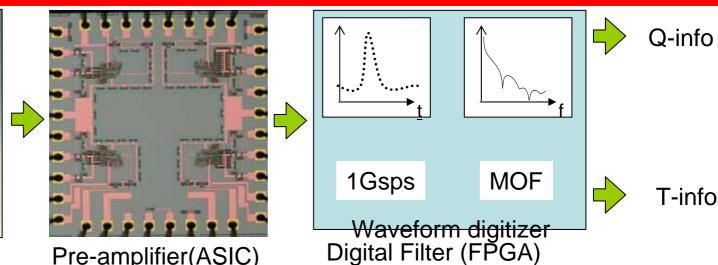
HPD system

HPDs

- \checkmark have a simple structure. \rightarrow lower cost than PMT and easy Quality control.
- \checkmark EB takes major role in e-amplification \rightarrow small statistical fluctuation
 - \rightarrow Small \triangle path of P.E. \rightarrow Better timing resolution
 - \rightarrow Small \triangle gain of P.E. \rightarrow Better S/N

\checkmark but lower gain \rightarrow a part of readout electronics implementation near HPD





13-inch HAPD

Pre-amplifier(ASIC)

Flexible & tolerant system for baseline instability electric & magnetic interferences from external environment (i.e. ripple of power supply, ground bounce, ground loop etc)

T&Q performances are evaluated using this system

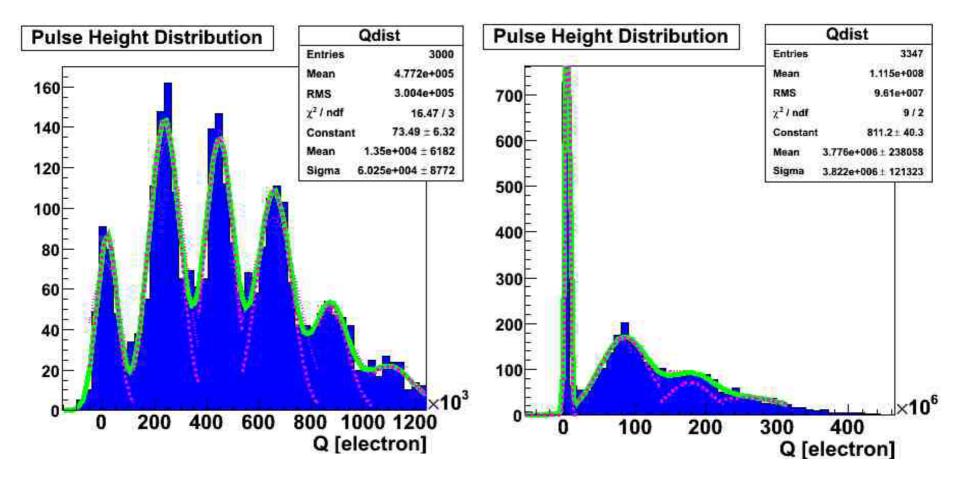
HPD performance(detail)

- Energy measurement related items
 - Comparison between HPD and PMT
 - Dynamic range
 - Position dependence of relative gain
- Timing measurement related items
 - Comparison & # of P.E. dependence
 - HV dependence
- Dark rate

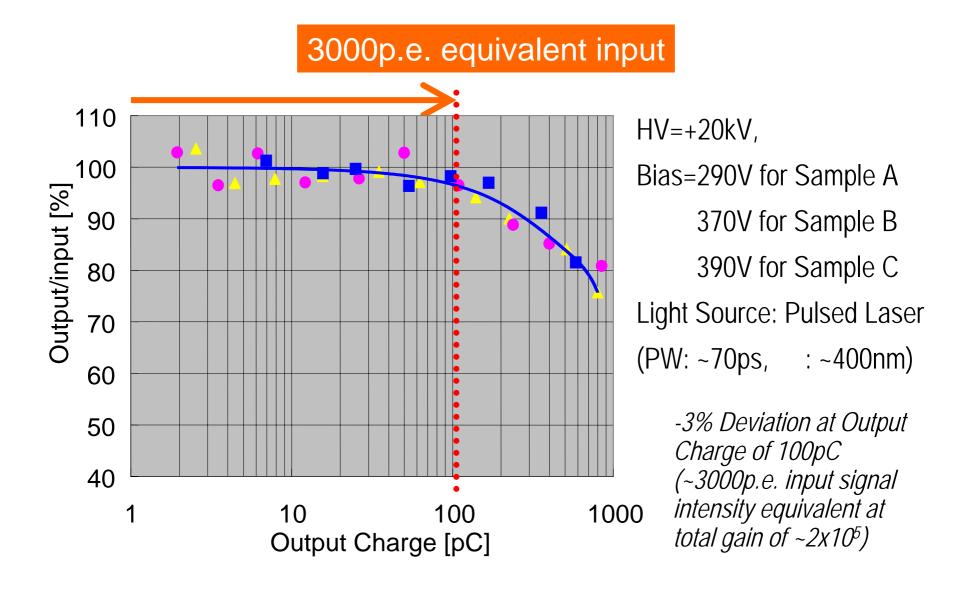
Comparison of HPD and PMT

HPD(HV=12kV bias=330V)

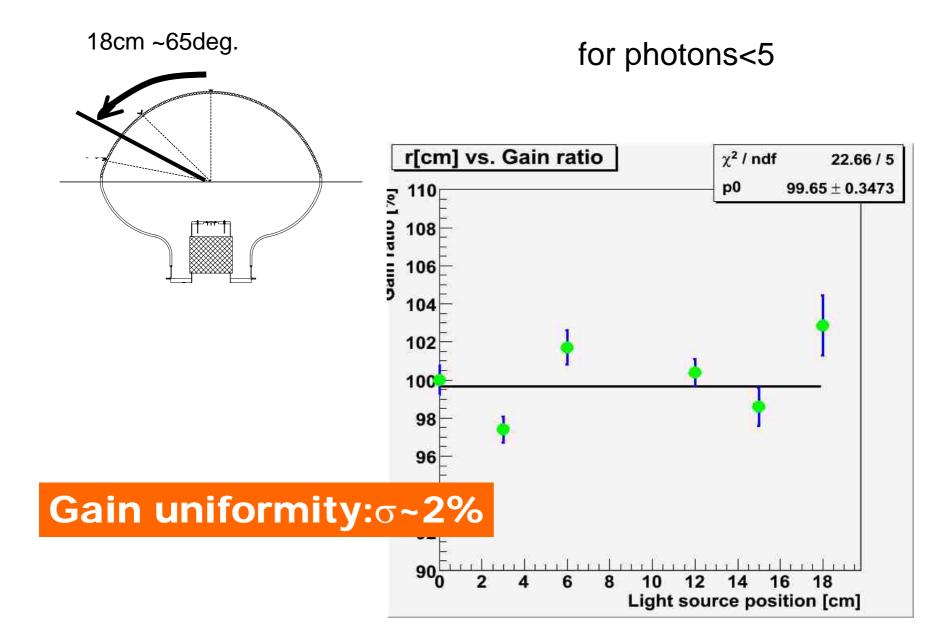
PMT(13inch)



Dynamic Range (no preamplifier)



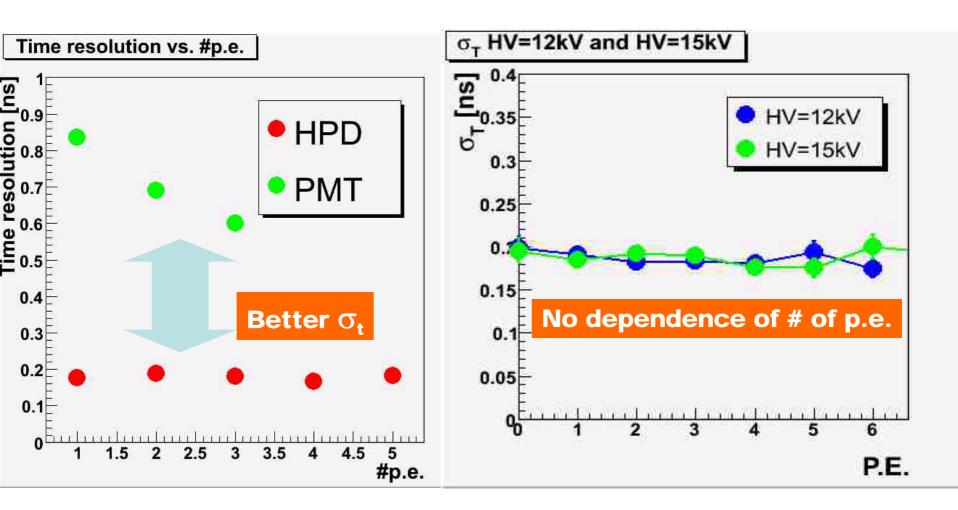
Position dependence of gain



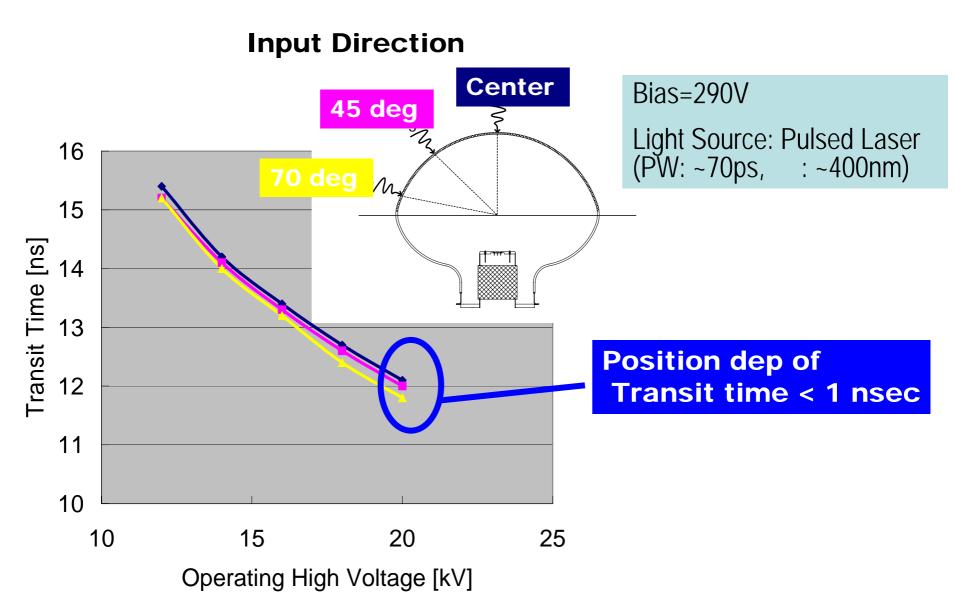
Timing resolution

Laser illuminated

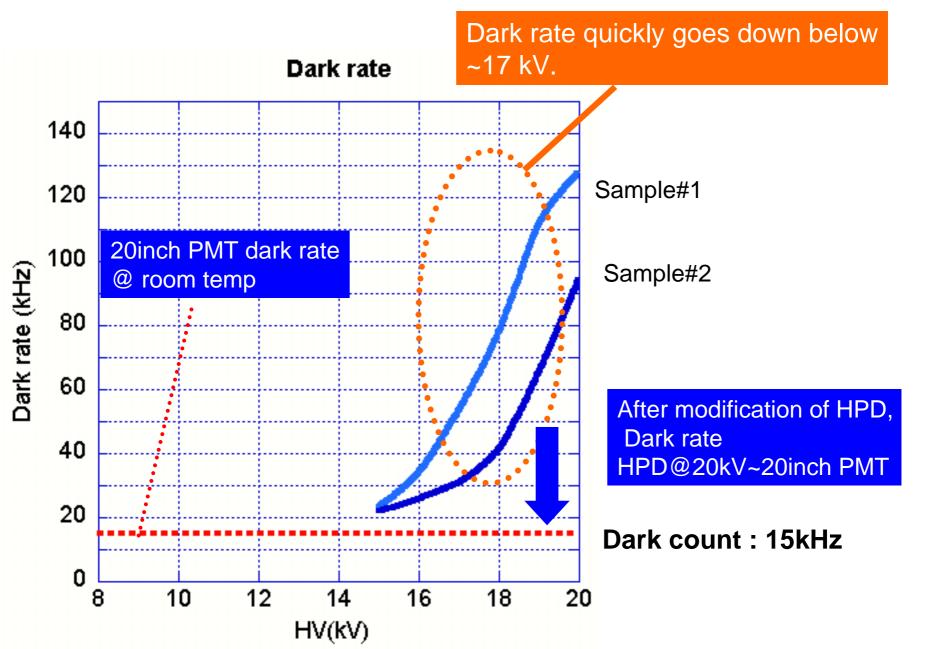
HV=12kV bias=330V



Photoelectron Transit Time



Dark rate

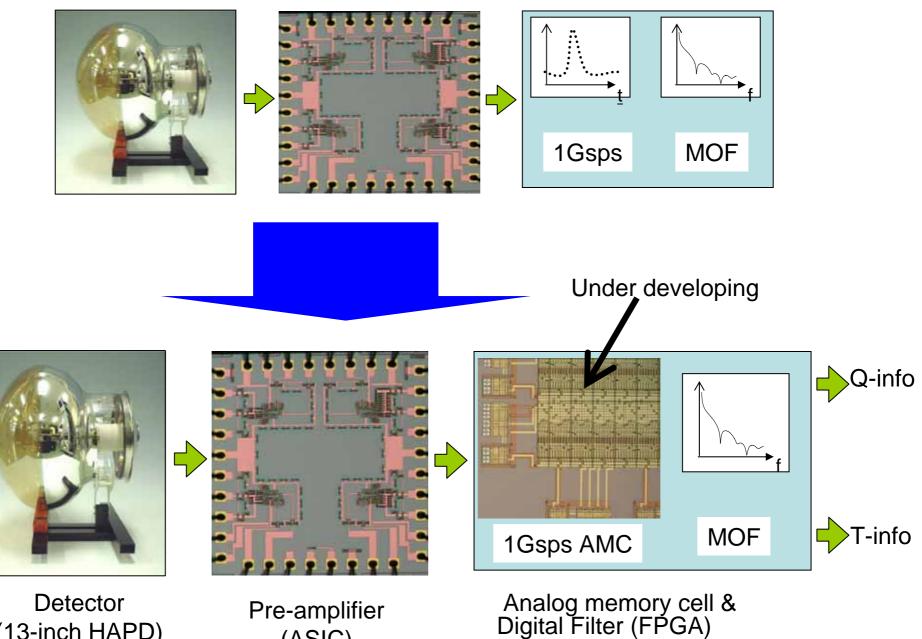


Comparison of Developed HPD and Conventional Large-Aperture PMTs

Parameters*		Developed HPD (13-inch HPD)	13-inch PMT (R8055)	20-inch PMT (R3600-02 for SK)
Order of Gain		10 ⁵	10 ⁷	10 ⁷
Single Photon Time Resolution (σ)		190ps	1400ps	2300ps
Single Photon Energy Resolution		44% (preliminary)	70%	150%
Pulse Response	Rise Time	1ns	6ns	10ns
	Pulse Width	2.2ns	10ns	20ns
Transient Time		12ns	100ns	95ns
Dynamic Range (Signal Intensity in p.e.)		3000 p.e.	2000 p.e.	1000 p.e.

* Únder rated operating voltage of 1.5kV for R8055 and 2kV for R3600-02. HV of +20kV bias voltage of 390V for HPD

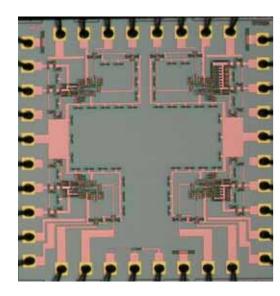
HPD electronics status

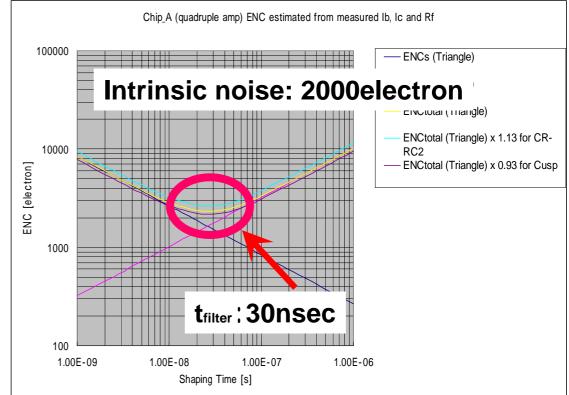


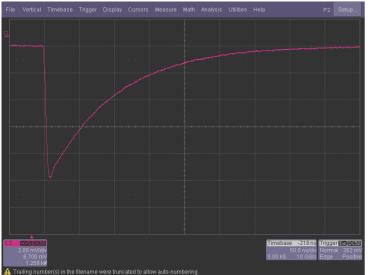
(13-inch HAPD)

Pre-amplifier (ASIC)

Front-end electronics

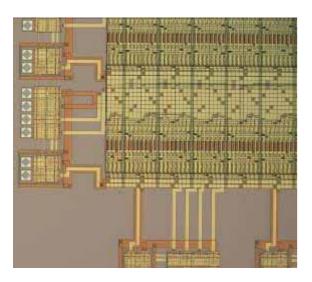




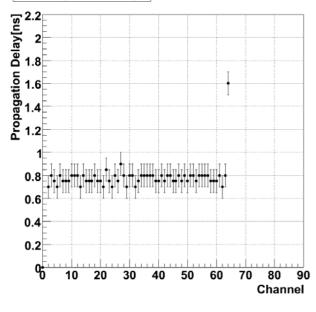


Rise time : < 1nsec Dynamic range: 2V Power consumption : ~4mW/ch (depends on driving capability)

Analog memory cell



Propagation Delay



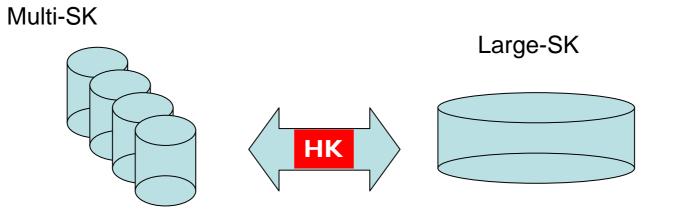


Performance (measured)

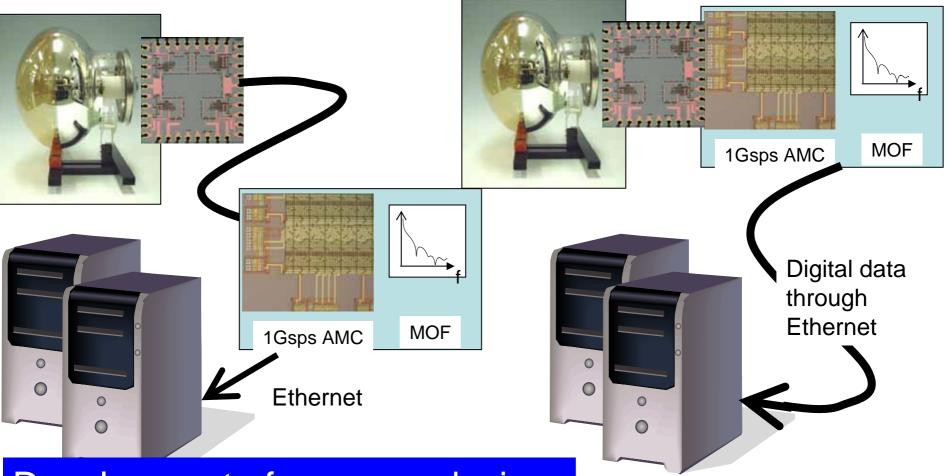
- Sampling period : 1Gsps
- Dynamic range : 3.5V
- Integral nonlinearity 0.1% for 2.5V
- Uniformity of sampling period <100ps
- 50mW/ch

HPD system in the next step

- In the next step (after several modifications)
 - Stability for temperature (for general purpose)
 - Evaluation of long term stability
 - Optimization of manufacturing process for production cost
 - Photocathode formation
 - Low cost material
 - Quality check during production
 - Customization of electronics/system for HK



• Similar to SK • On HPD



Development of common devices

After determination of timing I/F(i.e. trigger, clock ..) Multi-chip module or deep submicron ASIC (blue rectangle part) will be developed as a building block of the readout system.

Summary

We have developed a 13-inch HPD and confirmed <ru>

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✓ Total Gain of >2 x 10⁵

Promising as a photosensor for the next generation water-Cherenkov detector.

Next Steps

□ Optimization of manufacturing process

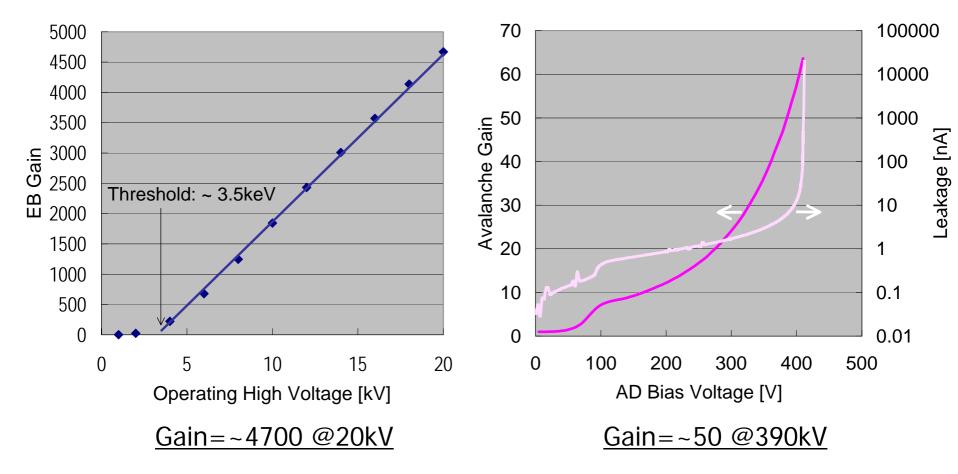
Evaluation of long-term operation stability

■ Readout electronics customization

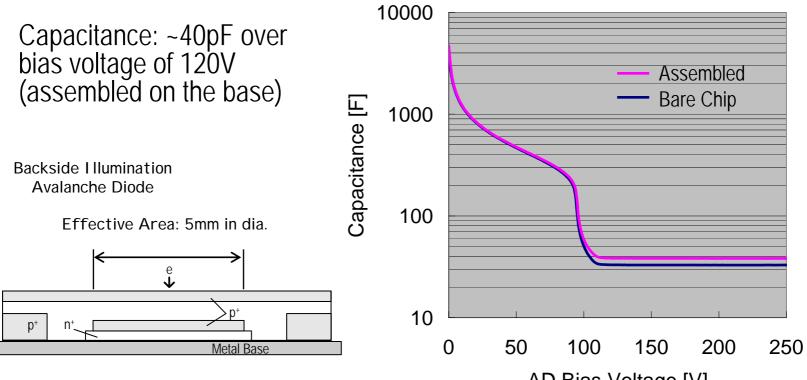
EB and Avalanche Gain

AD Bias=30V(fixed), HV=Swept

HV=+10kV(fixed), Bias=Swept



Incorporated Avalanche Diode and its C-V Characteristics



AD Bias Voltage [V]

Photoelectron Collection Efficiency and Effect of Magnetic Field (Simulation)

Photoelectron Collection Efficiency as Collection Efficiency as a function a function of HV (No Magnetic Field) of Magnetic Field (at HV of +20kV) 100 120 98 100 Collection Efficiency [%] 96 Parallel Perpendicular 94 80 92 90 60 88 40 86 84 20 Perpendicular 82 80 0 5 10 15 20 25 0.5 0

Operating High Voltage [kV]

Collection Efficiency [%]

Magnetic Field Intensity [Gauss]

Paralle

1.5